(19) World Intellectual Property Organization International Bureau



(43) International Publication Date 27 January 2005 (27.01.2005)

(10) International Publication Number WO 2005/008695 A2

(51) International Patent Classification?:

H01F 17/00

(21) International Application Number:

PCT/IB2004/051234

(22) International Filing Date:

15 July 2004 (15.07.2004)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

03102261.9

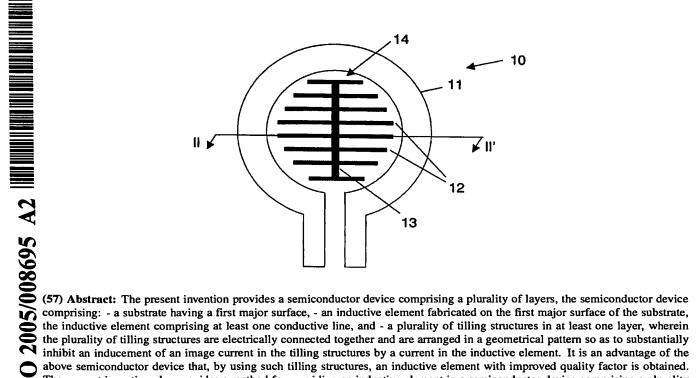
23 July 2003 (23.07.2003)

- (71) Applicant (for all designated States except US): KONIN-KLIJKE PHILIPS ELECTRONICS N.V. [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): DETCHEVERRY, Celine, J. [FR/BE]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). VAN NOORT, Wibo, D. [NL/BE]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).

- (74) Agent: ELEVELD, Koop, J.; Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).
- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CII, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

[Continued on next page]

(54) Title: INDUCTIVE AND CAPACITIVE ELEMENTS FOR SEMICONDUCTOR TECHNOLOGIES WITH MINIMUM PAT-TERN DENSITY REQUIREMENTS



above semiconductor device that, by using such tilling structures, an inductive element with improved quality factor is obtained. The present invention also provides a method for providing an inductive element in a semiconductor device comprising a plurality of layers.

WO 2005/008695 A2 | III | III

Declaration under Rule 4.17:

— as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SI, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE,

BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NI., PI., PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)

Published:

 without international search report and to be republished upon receipt of that report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.